imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



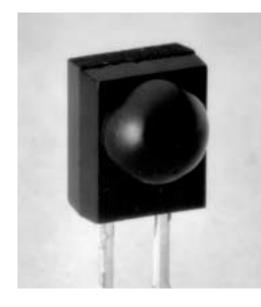
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VTP Process Photodiodes

VTP7840H



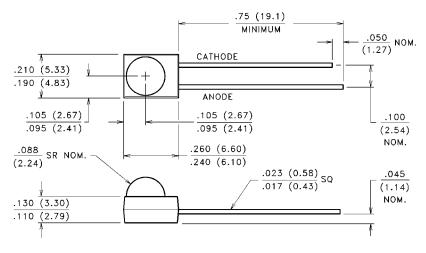
PRODUCT DESCRIPTION

response.

Planar silicon photodiode in a transfer molded,

large lensed sidelooker package. The dark package material filters out visible light but passes infrared. These diodes exhibit low dark current under reverse bias and fast speed of

PACKAGE DIMENSIONS inch (mm)



CASE 51 LENSED SIDELOOKER CHIP ACTIVE AREA: .0082 in² (5.27 mm²)

ABSOLUTE MAXIMUM RATINGS

Storage Temperature:	-40°C to 85°C
Operating Temperature:	-40°C to 85°C

RoHS Compliant



ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also VTP curves, pages 45-46)

SYMBOL	CHARACTERISTIC TEST CONDITIONS	VTP7840H				
		TEST CONDITIONS	Min.	Тур.	Max.	- UNITS
I _{SC}	Short Circuit Current	H = 100 fc, 2850 K	50	70		μA
TC I _{SC}	I _{SC} Temperature Coefficient	2850 K		.20		%/°C
V _{OC}	Open Circuit Voltage	H = 100 fc, 2850 K		325		mV
TC V _{OC}	V _{OC} Temperature Coefficient	2850 K		-2.0		
I _D	Dark Current	H = 0, VR = 10 V			20	nA
R _{SH}	Shunt Resistance	H = 0, V = 10 mV		0.25		GΩ
CJ	Junction Capacitance	H = 0, V = 3 V			40	pF
S _R	Sensitivity	@ Peak		.55		A/W
λ_{range}	Spectral Application Range		725		1150	nm
λρ	Spectral Response - Peak			925		nm
V _{BR}	Forward Voltage	@ 10 mA		1.0		V
$\theta_{1/2}$	Angular Resp 50% Resp. Pt.			±48		Degrees
NEP	Noise Equivalent Power			5.3 x 10 ⁻¹⁴ (Typ.)		W∕√Hz
D*	Specific Detectivity			5.1 x 10 ¹² (Typ.)		cm√Hz/W